CY7C1021CV33

1-Mbit (64K x 16) Static RAM

Features

- **Temperature Ranges**
  - **— Commercial: 0°C to 70°C**
  - **— Industrial: –40°C to 85°C**
  - **— Automotive-A: –40°C to 85°C**
  - **— Automotive-E: –40°C to 125°C**
- **Pin- and function-compatible with CY7C1021BV33**
- **High speed**
  - **— t_{AA} = 8 ns (Commercial & Industrial)**
  - **— t_{AA} = 12 ns (Automotive)**
- **CMOS for optimum speed/power**
- **Low active power: 345 mW (max.)**
- **Automatic power-down when deselected**
- **Independent control of upper and lower bits**
- **Available in Pb-free and non Pb-free 44-pin 400-Mil SOJ 44-pin TSOP II and 48-ball FBGA packages**

Functional Description[1]

The CY7C1021CV33 is a high-performance CMOS static RAM organized as 65,536 words by 16 bits. This device has an automatic power-down feature that significantly reduces power consumption when deselected.

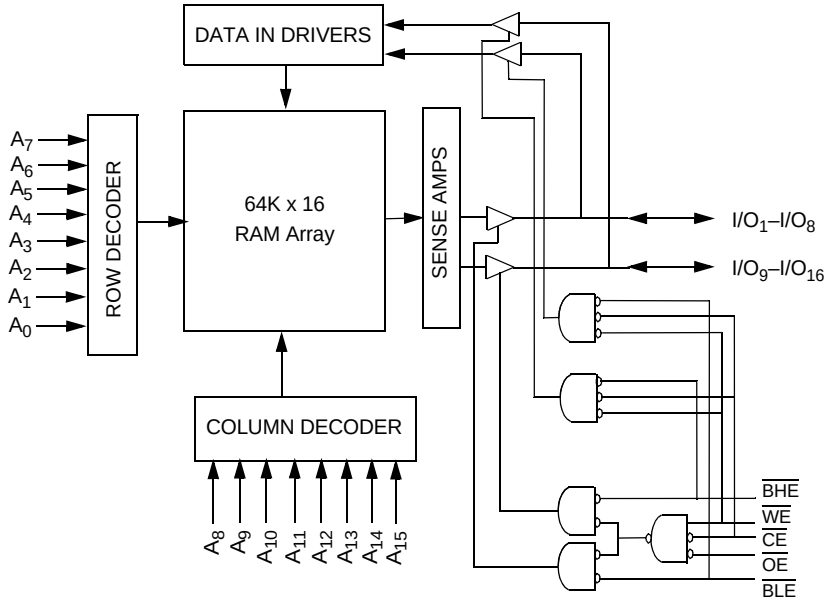
Writing to the device is accomplished by taking Chip Enable (CE) and Write Enable (WE) inputs LOW. If Byte Low Enable (BLE) is LOW, then data from I/O pins (I/O_1 through I/O_8), is written into the location specified on the address pins (A_0 through A_{15}). If Byte High Enable (BHE) is LOW, then data from I/O pins (I/O_9 through I/O_{16}) is written into the location specified on the address pins (A_0 through A_{15}).

Reading from the device is accomplished by taking Chip Enable (CE) and Output Enable (OE) LOW while forcing the Write Enable (WE) HIGH. If Byte Low Enable (BLE) is LOW, then data from the memory location specified by the address pins will appear on I/O_1 to I/O_8. If Byte High Enable (BHE) is LOW, then data from memory will appear on I/O_9 to I/O_{16}. See the truth table at the end of this data sheet for a complete description of Read and Write modes.

The input/output pins (I/O_1 through I/O_{16}) are placed in a high-impedance state when the device is deselected (CE HIGH), the outputs are disabled (OE HIGH), the BHE and BLE are disabled (BHE, BLE HIGH), or during a Write operation (CE LOW, and WE LOW).

The CY7C1021CV33 is available in 44-pin 400-Mil wide SOJ, 44-pin TSOP II and 48-ball FBGA packages.

Logic Block Diagram



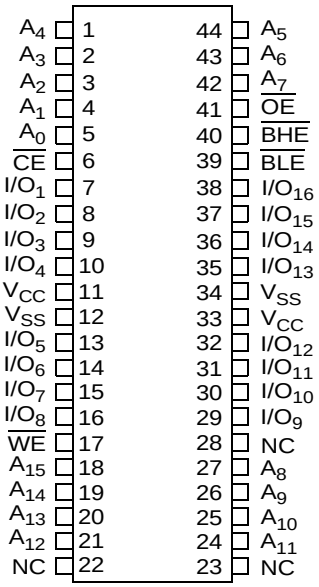
Note:
1. For best-practice recommendations, please refer to the Cypress application note “System Design Guidelines” on http://www.cypress.com.

Selection Guide

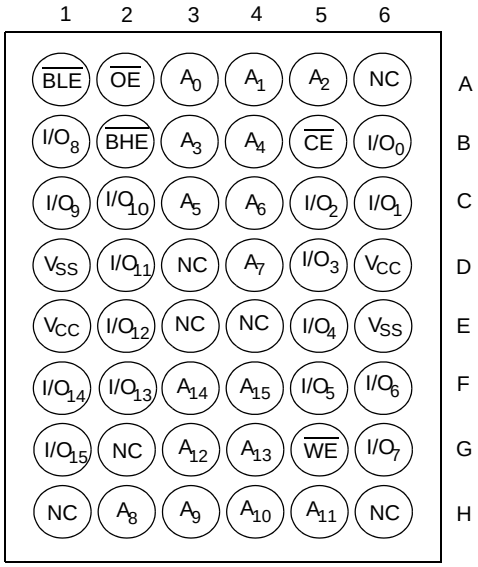
		-8	-10	-12	-15	Unit
Maximum Access Time		8	10	12	15	ns
Maximum Operating Current	Comm'l/Ind'l	95	90	85	80	mA
	Automotive-A				80	mA
	Automotive-E			90		mA
Maximum CMOS Standby Current	Comm'l/Ind'l	5	5	5	5	mA
	Automotive-A				5	mA
	Automotive-E			10		mA

Pin Configurations[2]

SOJ/TSOP II
Top View



48-ball FBGA
Top View



Note:
2. NC pins are not connected on the die.

Pin Definitions

Pin Name	SOJ, TSOP Pin Number	BGA Pin Number	I/O Type	Description
A_0–A_{15}	1–5, 18–21, 24–27, 42–44	A3, A4, A5, B3, B4, C3, C4, D4, H2, H3, H4, H5, G3, G4, F3, F4	Input	**Address Inputs used to select one of the address locations.**
I/O_0–I/O_{15}[3]	7–10, 13–16, 29–32, 35–38	B6, C6, C5, D5, E5, F5, F6, G6, B1, C1, C2, D2, E2, F2, F1, G1	Input/Output	**Bidirectional Data I/O lines**. Used as input or output lines depending on operation.
NC	22, 23, 28	A6, D3, E3, E4, G2, H1, H6	No Connect	**No Connects**. Not connected to the die.
$\overline{WE}$	17	G5	Input/Control	**Write Enable Input, active LOW**. When selected LOW, a Write is conducted. When deselected HIGH, a Read is conducted.
$\overline{CE}$	6	B5	Input/Control	**Chip Enable Input, active LOW**. When LOW, selects the chip. When HIGH, deselects the chip.
$\overline{BHE}$, $\overline{BLE}$	40, 39	B2, A1	Input/Control	**Byte Write Select Inputs, active LOW**. $\overline{BHE}$ controls I/O_{16}–I/O_9, $\overline{BLE}$ controls I/O_8–I/O_1.
$\overline{OE}$	41	A2	Input/Control	**Output Enable, active LOW**. Controls the direction of the I/O pins. When LOW, the I/O pins are allowed to behave as outputs. When deasserted HIGH, I/O pins are tri-stated, and act as input data pins.
V_{SS}	12,34	D1, E6	Ground	**Ground for the device**. Should be connected to ground of the system.
V_{CC}	11,33	D6, E1	Power Supply	**Power Supply inputs to the device.**

Note:
3. I/O_1–I/O_{16} for SOJ/TSOP and I/O_0–I/O_{15} for BGA packages.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....–65°C to +150°C

Ambient Temperature with Power Applied.....–55°C to +125°C

Supply Voltage on V_{CC} Relative to GND[4] ....–0.5V to +4.6V

DC Voltage Applied to Outputs in High-Z State[4] .....–0.5V to V_{CC}+0.5V

DC Input Voltage[4].....–0.5V to V_{CC}+0.5V

Current into Outputs (LOW) .....20 mA

Static Discharge Voltage.....>2001V (per MIL-STD-883, Method 3015)

Latch-up Current.....>200 mA

Operating Range

Range	Ambient Temperature (T_A)	V_{CC}
Commercial	0°C to +70°C	3.3V ± 10%
Industrial	–40°C to +85°C	
Automotive-A	–40°C to +85°C	
Automotive -E	–40°C to +125°C	

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		-8		-10		-12		-15		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = –4.0 mA		2.4		2.4		2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA			0.4		0.4		0.4		0.4	V
V_{IH}	Input HIGH Voltage			2.0	V_{CC} + 0.3	2.0	V_{CC} + 0.3	2.0	V_{CC} + 0.3	2.0	V_{CC} + 0.3	V
V_{IL}	Input LOW Voltage[4]			–0.3	0.8	–0.3	0.8	–0.3	0.8	–0.3	0.8	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}	Com'l/Ind'l	–1	+1	–1	+1	–1	+1	–1	+1	µA
			Auto-A							–1	+1	
			Auto-E					–12	+12			
I_{OZ}	Output Leakage Current	GND ≤ V_I ≤ V_{CC}, Output Disabled	Com'l/Ind'l	–1	+1	–1	+1	–1	+1	–1	+1	µA
			Auto-A							–1	+1	
			Auto-E					–12	+12			
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., I_{OUT} = 0 mA, f = f_{MAX} = $1/t_{RC}$	Com'l/Ind'l		95		90		85		80	mA
			Auto-A								80	mA
			Auto-E						90			
I_{SB1}	Automatic CE Power-Down Current —TTL Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH} V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}	Com'l/Ind'l		15		15		15		15	mA
			Auto-A								15	
			Auto-E						20			
I_{SB2}	Automatic CE Power-Down Current —CMOS Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{CC} – 0.3V, V_{IN} ≥ V_{CC} – 0.3V, or V_{IN} ≤ 0.3V, f = 0	Com'l/Ind'l		5		5		5		5	mA
			Auto-A								5	
			Auto-E						10			

Note:
4. V_{IL} (min.) = –2.0V and V_{IH}(max) = V_{CC} + 0.5V for pulse durations of less than 20 ns.

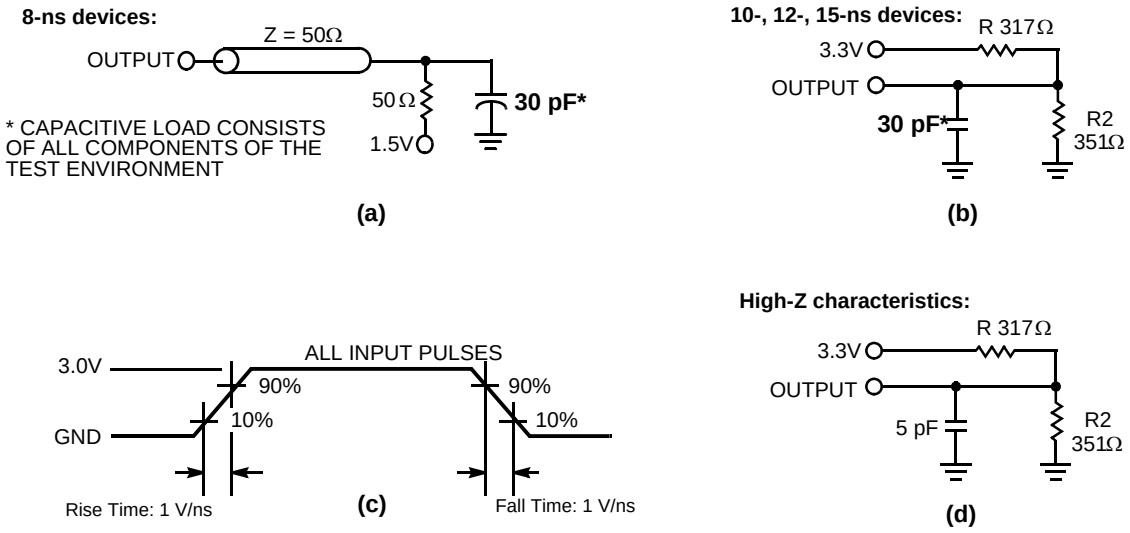
Capacitance[5]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 3.3V	8	pF
C_{OUT}	Output Capacitance		8	pF

Thermal Resistance[5]

Parameter	Description	Test Conditions	SOJ	TSOP II	FBGA	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA/JESD51	65.06	76.92	95.32	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		34.21	15.86	10.68	°C/W

AC Test Loads and Waveforms[6]



Notes:
5. Tested initially and after any design or process changes that may affect these parameters.
6. AC characteristics (except High-Z) for all 8-ns parts are tested using the load conditions shown in Figure (a). All other speeds are tested using the Thevenin load shown in Figure (b). High-Z characteristics are tested for all speeds using the test load shown in Figure (d).

Switching Characteristics Over the Operating Range[7]

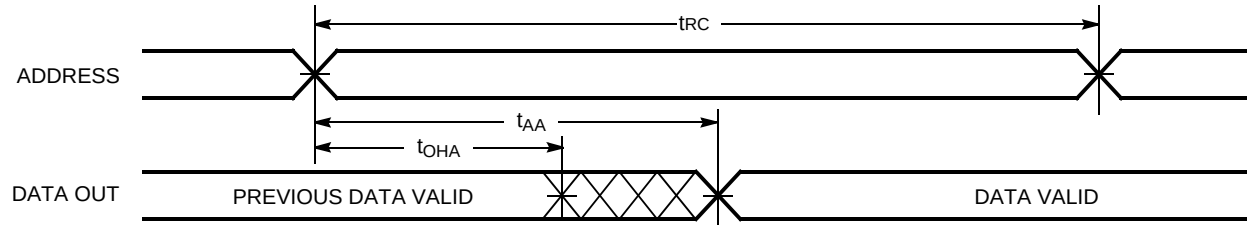
Parameter	Description	-8		-10		-12		-15		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle										
t_{power}[8]	V_{CC}(typical) to the first access	100		100		100		100		µs
t_{RC}	Read Cycle Time	8		10		12		15		ns
t_{AA}	Address to Data Valid		8		10		12		15	ns
t_{OHA}	Data Hold from Address Change	3		3		3		3		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		8		10		12		15	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		5		5		6		7	ns
t_{LZOE}	$\overline{OE}$ LOW to Low-Z[9]	0		0		0		0		ns
t_{HZOE}	$\overline{OE}$ HIGH to High-Z[9, 10]		4		5		6		7	ns
t_{LZCE}	$\overline{CE}$ LOW to Low-Z[9]	3		3		3		3		ns
t_{HZCE}	$\overline{CE}$ HIGH to High-Z[9, 10]		4		5		6		7	ns
t_{PU}[11]	$\overline{CE}$ LOW to Power-Up	0		0		0		0		ns
t_{PD}[11]	$\overline{CE}$ HIGH to Power-Down		8		10		12		15	ns
t_{DBE}	Byte Enable to Data Valid		5		5		6		7	ns
t_{LZBE}	Byte Enable to Low-Z	0		0		0		0		ns
t_{HZBE}	Byte Disable to High-Z		4		5		6		7	ns
Write Cycle[12]										
t_{WC}	Write Cycle Time	8		10		12		15		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	7		8		9		10		ns
t_{AW}	Address Set-up to Write End	7		8		9		10		ns
t_{HA}	Address Hold from Write End	0		0		0		0		ns
t_{SA}	Address Set-up to Write Start	0		0		0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	6		7		8		10		ns
t_{SD}	Data Set-up to Write End	5		5		6		8		ns
t_{HD}	Data Hold from Write End	0		0		0		0		ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z[9]	3		3		3		3		ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z[9, 10]		4		5		6		7	ns
t_{BW}	Byte Enable to End of Write	6		7		8		9		ns

Notes:

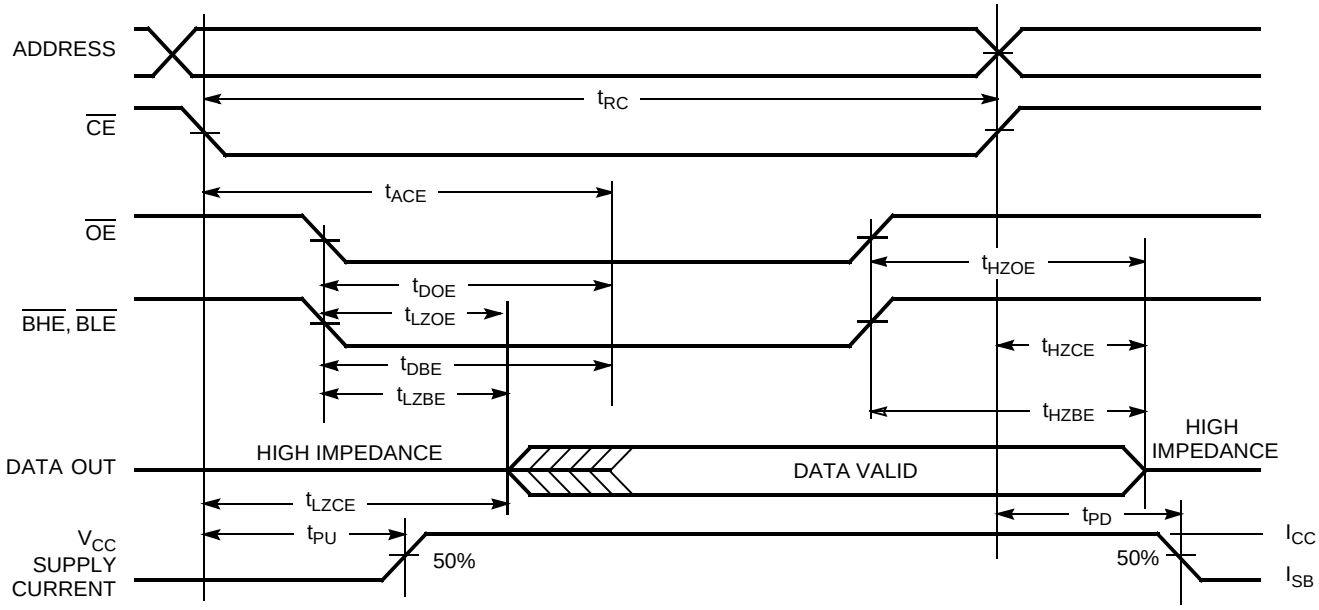
7. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V.
8. t_{POWER} gives the minimum amount of time that the power supply should be at typical V_{CC} values until the first memory access is performed.
9. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
10. t_{HZOE}, t_{HZBE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (d) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
11. This parameter is guaranteed by design and is not tested.
12. The internal Write time of the memory is defined by the overlap of $\overline{CE}$ LOW, $\overline{WE}$ LOW and $\overline{BHE}$/$\overline{BLE}$ LOW. $\overline{CE}$, $\overline{WE}$ and $\overline{BHE}$/$\overline{BLE}$ must be LOW to initiate a Write, and the transition of these signals can terminate the Write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the Write.

Switching Waveforms

Read Cycle No. 1 (Address Transition Controlled)[13, 14]



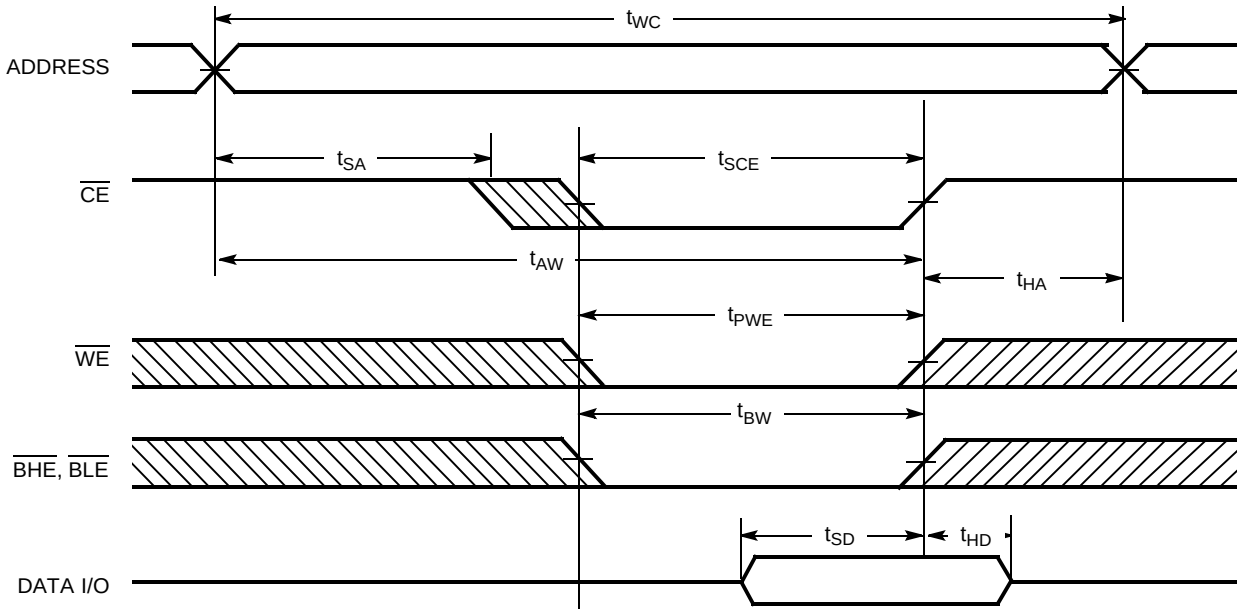
Read Cycle No. 2 ($\overline{OE}$ Controlled)[14, 15]



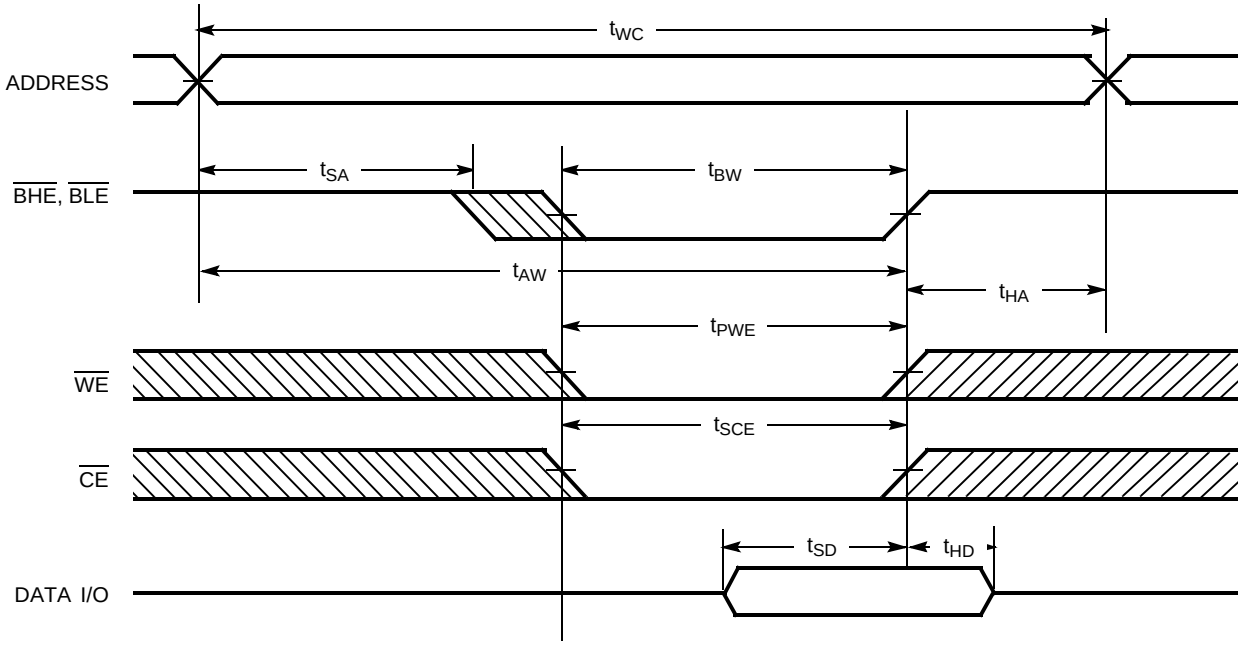
Notes:
13. Device is continuously selected. $\overline{OE}$, $\overline{CE}$, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL}.
14. $\overline{WE}$ is HIGH for Read cycle.
15. Address valid prior to or coincident with $\overline{CE}$ transition LOW.

Switching Waveforms (continued)

Write Cycle No. 1 ($\overline{CE}$ Controlled)[16, 17]



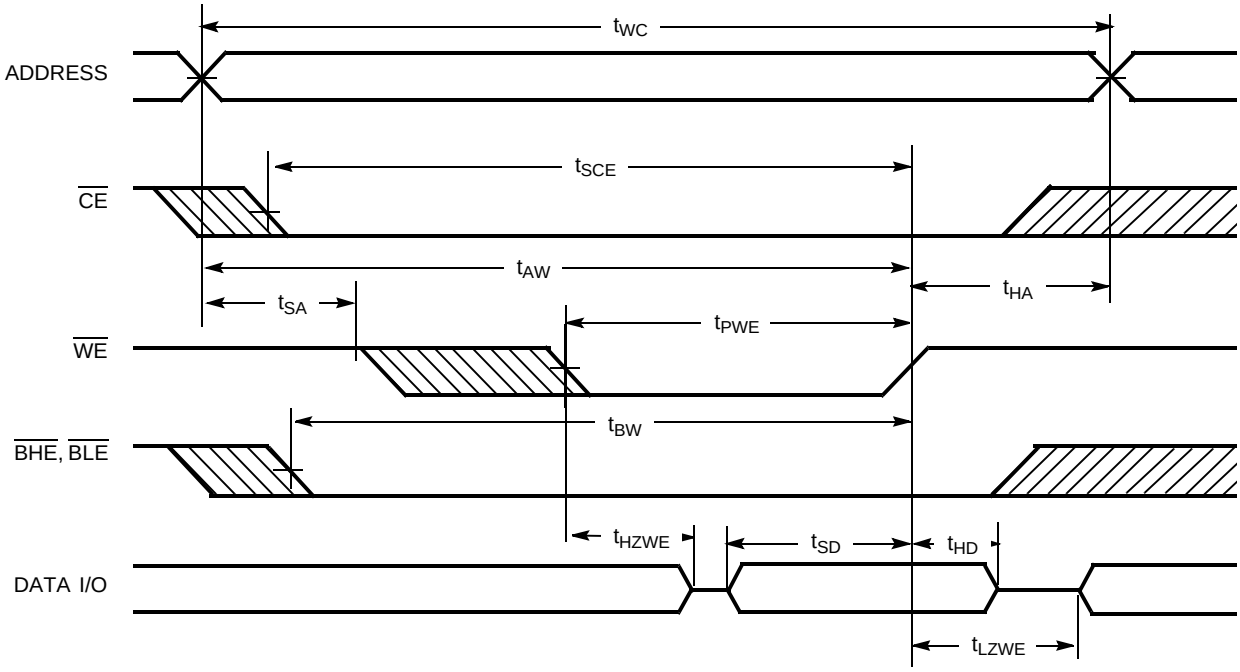
Write Cycle No. 2 ($\overline{BLE}$ or $\overline{BHE}$ Controlled)



Notes:
16. Data I/O is high impedance if $\overline{OE}$ or $\overline{BHE}$ and/or $\overline{BLE}$= V_{IH}.
17. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ going HIGH, the output remains in a high-impedance state.

Switching Waveforms (continued)

Write Cycle No. 3 ($\overline{WE}$ Controlled, LOW)



Truth Table

$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	$\overline{BLE}$	$\overline{BHE}$	I/O_1–I/O_8[3]	I/O_9–I/O_{16}[3]	Mode	Power
H	X	X	X	X	High-Z	High-Z	Power-down	Standby (I_{SB})
L	L	H	L	L	Data Out	Data Out	Read – All bits	Active (I_{CC})
			L	H	Data Out	High-Z	Read – Lower bits only	Active (I_{CC})
			H	L	High-Z	Data Out	Read – Upper bits only	Active (I_{CC})
L	X	L	L	L	Data In	Data In	Write – All bits	Active (I_{CC})
			L	H	Data In	High-Z	Write – Lower bits only	Active (I_{CC})
			H	L	High-Z	Data In	Write – Upper bits only	Active (I_{CC})
L	H	H	X	X	High-Z	High-Z	Selected, Outputs Disabled	Active (I_{CC})
L	X	X	H	H	High-Z	High-Z	Selected, Outputs Disabled	Active (I_{CC})

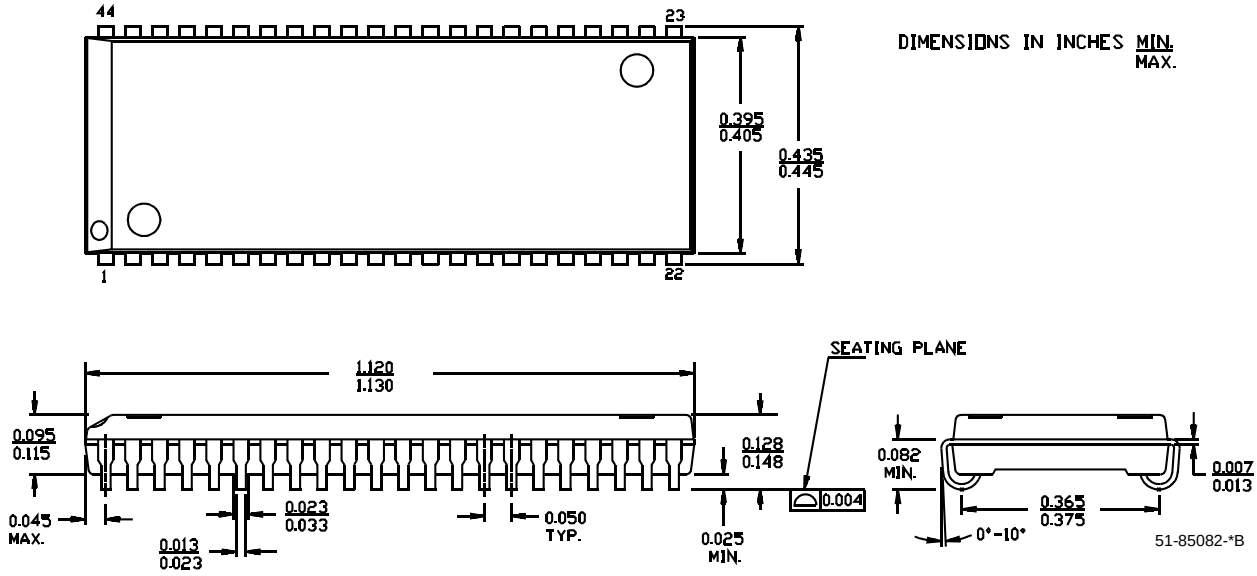
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
8	CY7C1021CV33-8VXC	51-85082	44-pin (400-Mil) Molded SOJ (Pb-free)	Commercial
	CY7C1021CV33-8ZXC		44-pin TSOP Type II (Pb-free)	
	CY7C1021CV33-8BAXC	51-85096	48-ball FBGA (Pb-free)	
10	CY7C1021CV33-10VC	51-85082	44-pin (400-Mil) Molded SOJ	Commercial
	CY7C1021CV33-10VXC		44-pin (400-Mil) Molded SOJ (Pb-free)	
	CY7C1021CV33-10ZXC	51-85087	44-pin TSOP Type II (Pb-free)	
	CY7C1021CV33-10ZI		44-pin TSOP Type II	Industrial
	CY7C1021CV33-10ZXI		44-pin TSOP Type II (Pb-free)	
	CY7C1021CV33-10BAXI	51-85096	48-ball FBGA (Pb-free)	
12	CY7C1021CV33-12VC	51-85082	44-pin (400-Mil) Molded SOJ	Commercial
	CY7C1021CV33-12VXC		44-pin (400-Mil) Molded SOJ (Pb-free)	
	CY7C1021CV33-12VI		44-pin (400-Mil) Molded SOJ	Industrial
	CY7C1021CV33-12VXI		44-pin (400-Mil) Molded SOJ (Pb-free)	
	CY7C1021CV33-12ZXC	51-85087	44-pin TSOP Type II (Pb-free)	Commercial
	CY7C1021CV33-12ZXI		44-pin TSOP Type II (Pb-free)	Industrial
	CY7C1021CV33-12BAI	51-85096	48-ball FBGA	Industrial
	CY7C1021CV33-12BAXI		48-ball FBGA (Pb-free)	
	CY7C1021CV33-12ZSE	51-85087	44-pin TSOP Type II	Automotive-E
	CY7C1021CV33-12ZSXE		44-pin TSOP Type II (Pb-free)	
	CY7C1021CV33-12VE	51-85082	44-pin (400-Mil) Molded SOJ	
	CY7C1021CV33-12VXE		44-pin (400-Mil) Molded SOJ (Pb-free)	
	CY7C1021CV33-12BAE	51-85096	48-ball FBGA	
15	CY7C1021CV33-15VXC	51-85082	44-pin (400-Mil) Molded SOJ (Pb-free)	Commercial
	CY7C1021CV33-15ZXC	51-85087	44-pin TSOP Type II (Pb-free)	Commercial
	CY7C1021CV33-15ZI		44-pin TSOP Type II	Industrial
	CY7C1021CV33-15ZXI		44-pin TSOP Type II (Pb-free)	
	CY7C1021CV33-15BAXI	51-85096	48-ball FBGA (Pb-free)	
	CY7C1021CV33-15ZSXA	51-85087	44-pin TSOP Type II (Pb-free)	Automotive-A

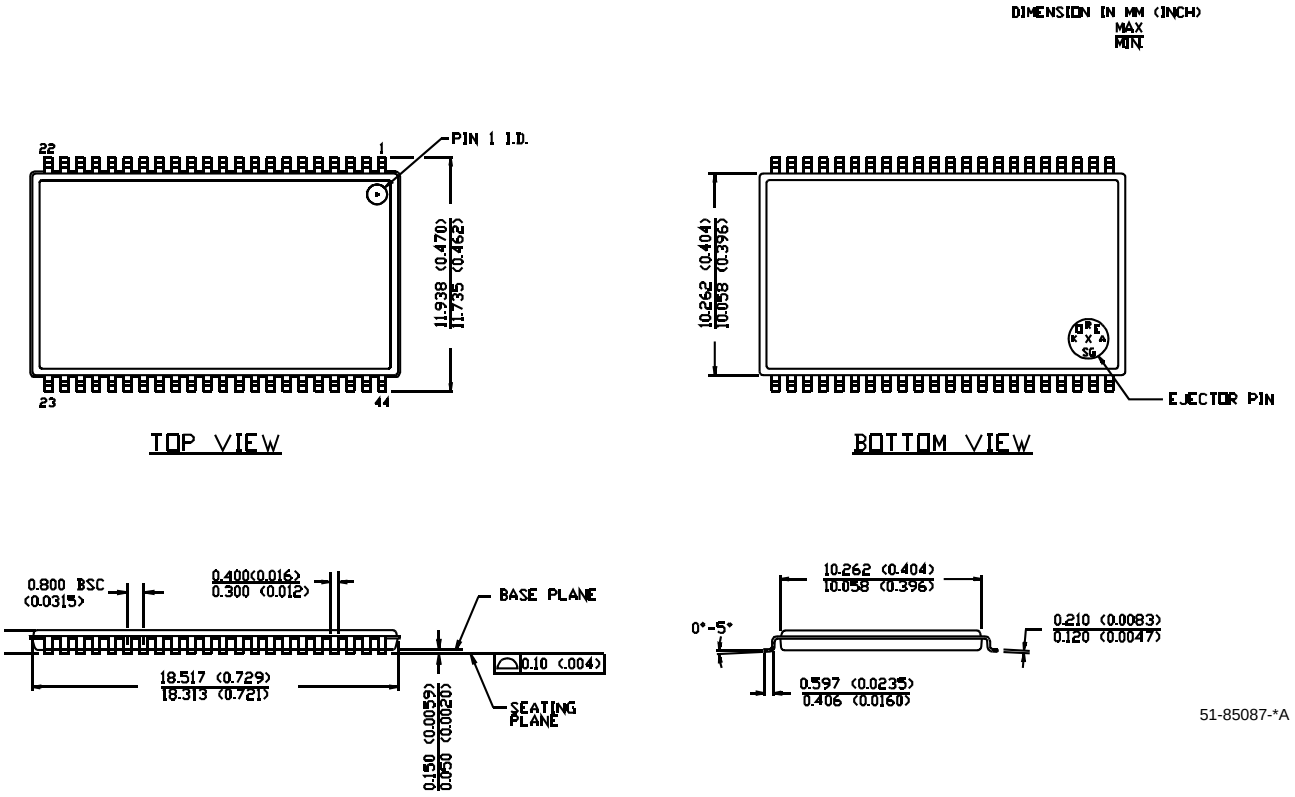
Please contact local sales representative regarding availability of these parts

Package Diagrams

44-pin (400-Mil) Molded SOJ (51-85082)

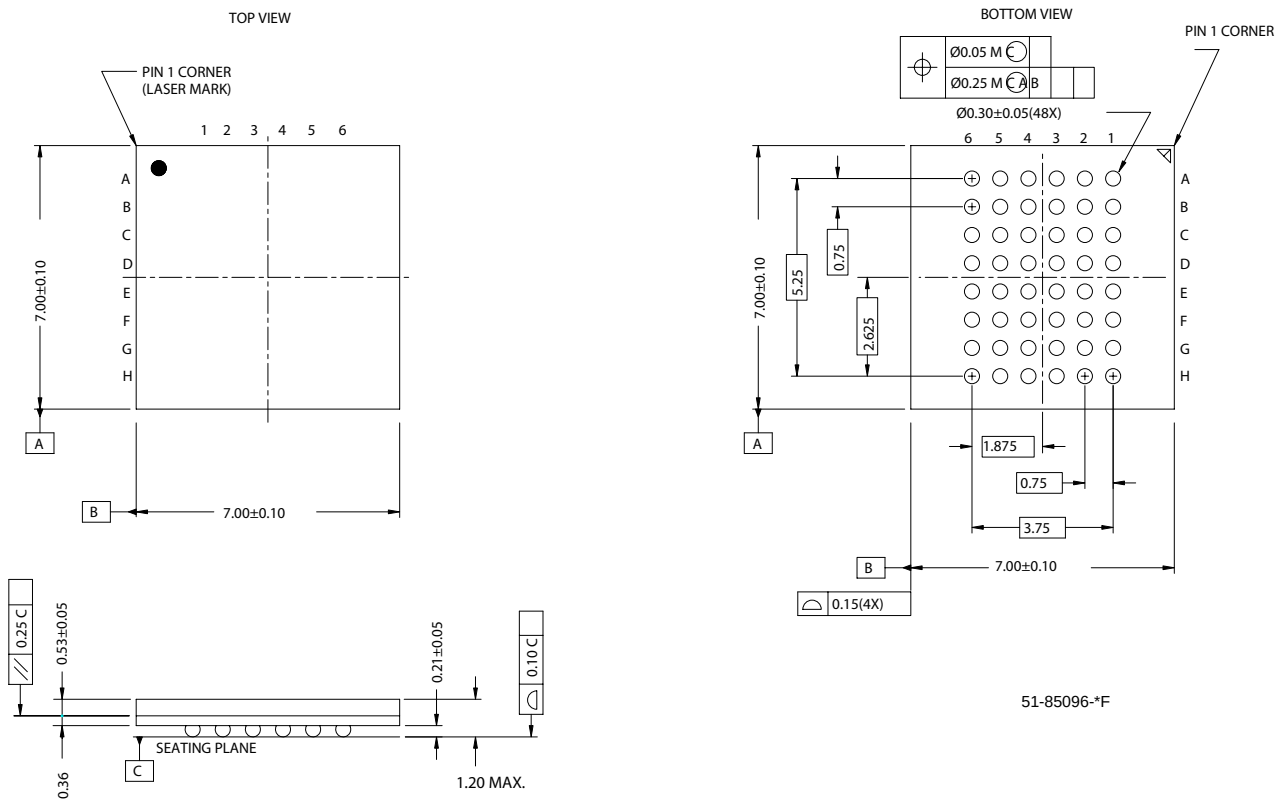


44-pin Thin Small Outline Package Type II (51-85087)



Package Diagrams (continued)

48-ball FBGA (7 x 7 x 1.2 mm) (51-85096)



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Document History Page

Document Title: CY7C1021CV33, 1-Mbit (64K x 16) Static RAM Document Number: 38-05132				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	109472	12/06/01	HGK	New Data Sheet
*A	115044	05/08/02	HGK	Ram7 version C4K x 16 Async Remove “Preliminary”
*B	115808	06/25/02	HGK	I_{SB1} and I_{CC} values changed
*C	120413	10/31/02	DFP	Updated BGA pin E4 to NC
*D	238454	See ECN	RKF	1) Added Automotive Specs to Data sheet 2) Added Pb-free devices in the Ordering Information
*E	334398	See ECN	SYT	Added Pb-free on page# 9 and 10
*F	493565	See ECN	NXR	Added Automotive-A operating range Corrected typo in the Pin Definition table Changed the description of I_{IX} from Input Load Current to Input Leakage Current in DC Electrical Characteristics table Removed I_{OS} parameter from DC Electrical Characteristics table Updated the ordering information table
*G	563963	See ECN	VKN	Added t_{POWER} spec in the AC Switching Characteristics table Added footnote #8